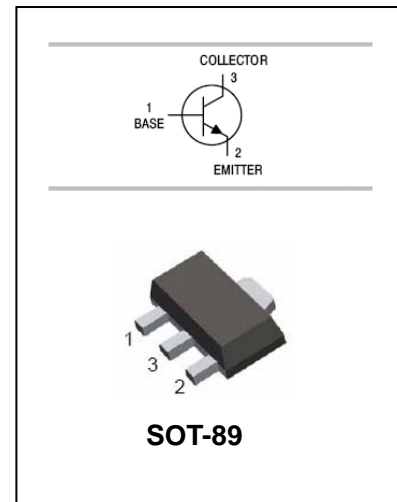


## SILICON PNP EPITAXIAL TYPE TRANSISTOR

HM879

### FEATURES

- Charger-up time is about 1 mS faster Than of a germanium transistor.
- Small saturation voltage can bring dissipation And flasing times.



### ORDERING INFORMATION

Type No.	Marking	Package Code
HM879	879	SOT-89

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>CEX</sub>	Collector-Emitter Voltage	20	V
V <sub>CEO</sub>	Collector-Emitter Voltage	10	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current –Continuous –Pluse	3 5	A
P <sub>C</sub>	Collector Dissipation	1	W
T <sub>j</sub> , T <sub>stg</sub>	Junction and Storage Temperature	-55 to +150	°C



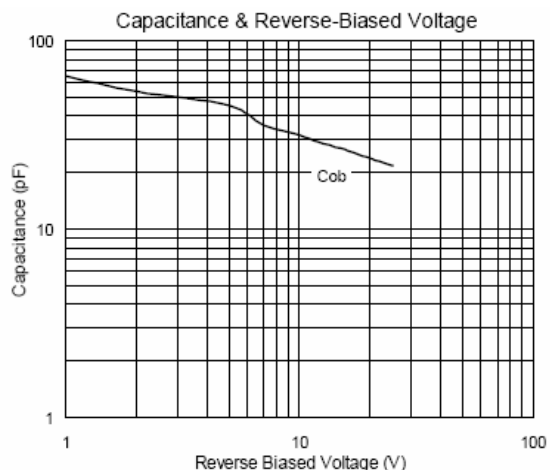
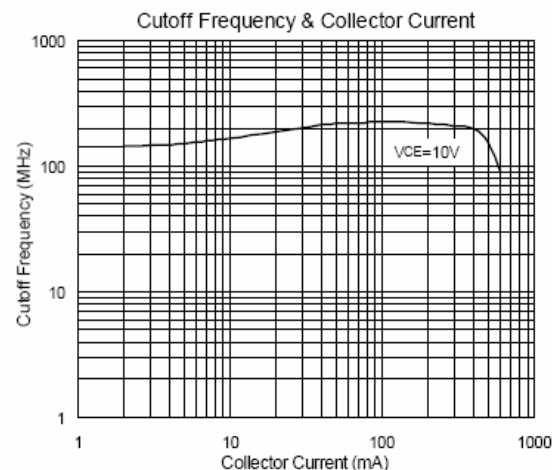
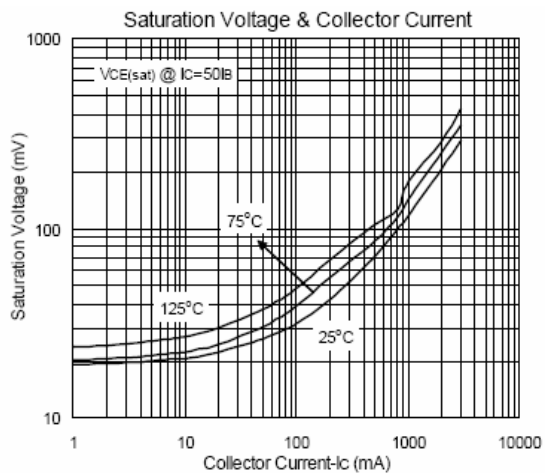
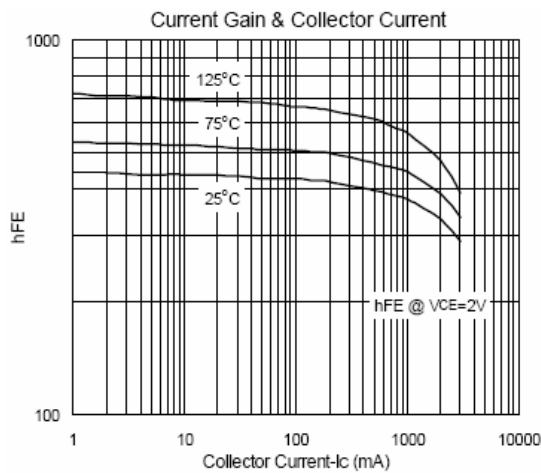
**SILICON PNP EPITAXIAL TYPE TRANSISTOR**

**HM879**

**ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	10			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector to Emitter Voltage	$V_{(BR)CEX}$	$I_C=1mA, V_{BE}=3V$	20			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=20V, I_E=0$			100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4V, I_C=0$			100	nA
DC current gain	$h_{FE}$	$V_{CE}=2V, I_C=3A$	140	210	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3A, I_B=60mA$		0.3	0.4	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=50mA$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$		30		pF

**TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**





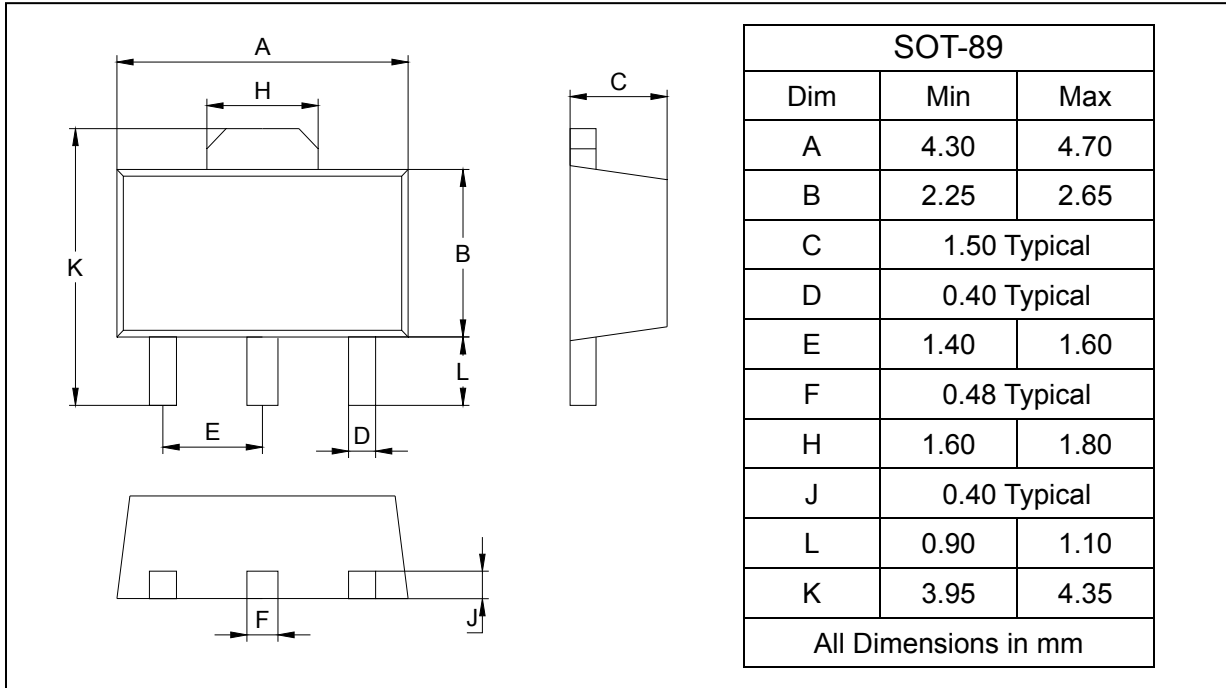
**SILICON PNP EPITAXIAL TYPE TRANSISTOR**

**HM879**

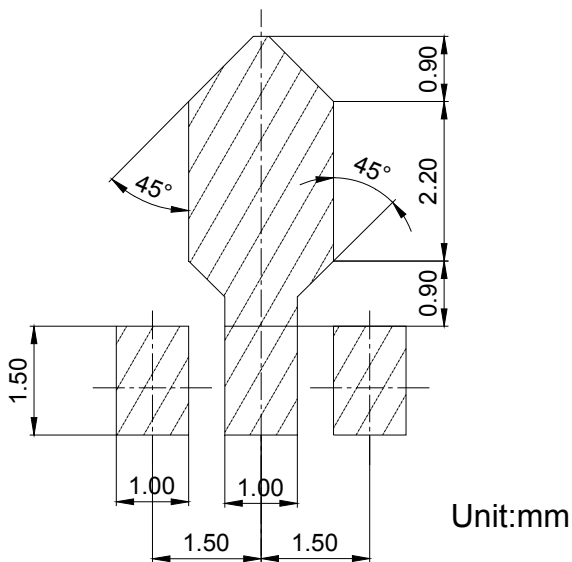
**PACKAGE OUTLINE**

Plastic surface mounted package

SOT-89



**SOLDERING FOOTPRINT**



**PACKAGE INFORMATION**

Device	Package	Shipping
HM879	SOT-89	1000/Tape&Reel